

B1  
cancel  
after treating the conductive liner with hydrogen, filling said hole with a  
conductive metal.

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Cancel Claim 2. ✓

Amend claim 9 to read as follows:

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9. (amended) A method for forming a contact in an integrated circuit, comprising  
the steps of:

B2  
forming a dielectric layer over a semiconductor body;  
etching a contact hole extending through said dielectric layer;  
depositing titanium over said dielectric layer, including on exposed  
surfaces within said contact hole;  
annealing said titanium;  
treating said titanium with hydrogen;  
depositing TiN over said titanium; and  
then, filling said contact hole with tungsten.

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